

ABSTRACT

The process of the present invention comprises reactive ion etching of $\text{Al}_x\text{F}_y\text{O}_z$ oxide deposits on aluminum-containing bond pads using feed gases, such as, $\text{SF}_6/\text{CF}_4/\text{Ar}$ or $\text{Cl}_2/\text{BCL}_3/\text{Ar}$. whose active plasma etches the $\text{Al}_x\text{F}_y\text{O}_z$ oxide deposits by physical etching and chemical etching for more complete removal of the $\text{Al}_x\text{F}_y\text{O}_z$ oxide deposits.